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N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{(BR)DSS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)	
200	0.122 at V _{GS} = 10 V	25	

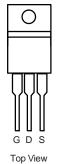
FEATURES

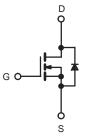


COMPLIANT

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_{g} and UIS tested

TO-220AB





N-Channel MOSFET

APPLICATIONS

- LCD/LED TV
- Consumer Appliances
- Lighting
- AC-DC Power Supply

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	200	V		
Gate-Source Voltage	V_{GS}	± 20	v		
Continuous Drain Current	V_{GS} at 10 V $\frac{T_C = 25 \text{ °C}}{T_C = 100 \text{ °C}}$	- I _D	25 ^a		
	$T_C = 100 ^{\circ}C$		18 ^a	Α	
Pulsed Drain Current		I _{DM}	100	I	
Single Pulse Avalanche Energy	E _{AS}	365	mJ		
Avalanche Current	I _{AR}	25	Α		
Repetiitive Avalanche Energy		E _{AR}	14	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	3.1 ^c	W	
	T _A = 25 °C ^b	T FD	130	T VV	
Peak Diode Recovery dV/dt	dV/dt	5.0	V/ns		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)	for 10 s		300	1	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYP.	MAX.	UNIT	
Maximum Junction-to-Ambient (PCB Mounted, Steady-State)	R _{thJA}	-	65	°C/W	
Maximum Junction-to-Case (Drain)	R _{thJC}	-	4.98		

- a. Package limited.
- b. When Mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				1		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	-	4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 160 V, V _{GS} = 0 V	-	-	1	- μΑ
	I _{DSS}	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 ^{\circ}\text{C}$	-	-	100	
		$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	=	-	2	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	25	-	-	Α
Drain-Source On-State Resistance a	D	V _{GS} = 10 V, I _D = 10 A	-	0.122	0.145	Ω
	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 8 A	-	0.135	0.158	
Forward Transconductance a	9 _{fs}	V _{DS} = 20 V, I _D = 10 A	-	15	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 160 V, f = 1 MHz	-	2450	-	pF
Output Capacitance	Coss			350		
Reverse Transfer Capacitance	C _{rss}		-	90	-	
Total Gate Charge ^c	Qg		=	25	41	nC
Gate-Source Charge ^c	Q _{gs}	V _{DS} = 160 V, V _{GS} = 10 V, I _D = 10 A		4.5		
Gate-Drain Charge ^c	Q_{gd}			13		
Gate Resistance	R_g	f = 1 MHz		3.9		Ω
Turn-On Delay Time ^c	t _{d(on)}			15	26	
Rise Time ^c	t _r	V_{DD} = 160 V, R_L = 1.67 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		25	44	ns
Turn-Off Delay Time ^c	t _{d(off)}		-	27	54	
Fall Time ^c	t _f		-	9	20	
Drain-Source Body Diode Ratings a	nd Characteris	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 μs)	I _{SM}		-	-	100	Α
Forward Voltage a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.75	1.5	V
Reverse Recovery Time	t _{rr}		i	88	176	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 20 \text{ A, d/dt} = 100 \text{ A/}\mu\text{s}$	=	5	10	Α
Reverse Recovery Charge	Q_{rr}		_	0.22	0.44	μC

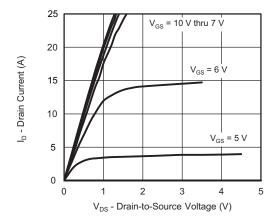
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

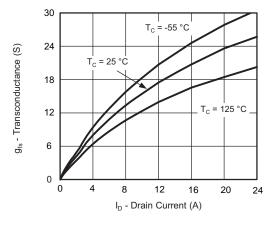
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



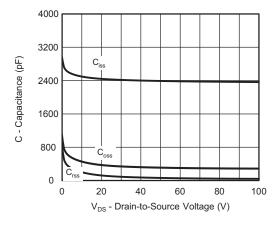
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



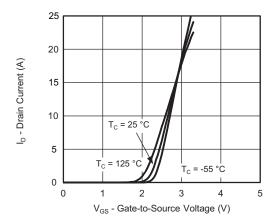
Output Characteristics



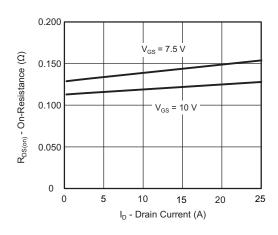
Transconductance



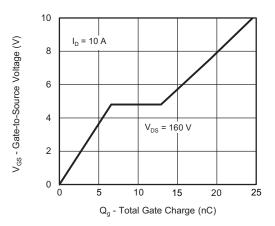
Capacitance



Transfer Characteristics



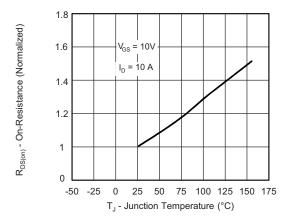
On-Resistance vs. Drain Current



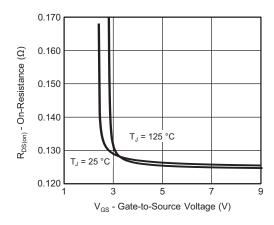
Gate Charge



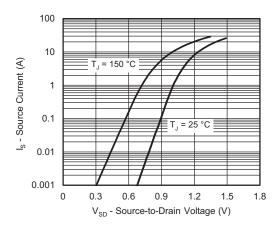
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



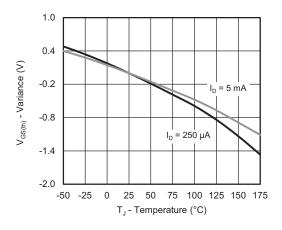
On-Resistance vs. Junction Temperature



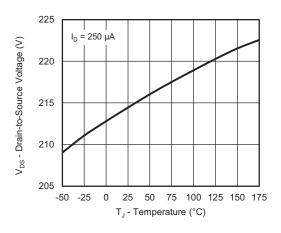
On-Resistance vs. Gate-to-Source Voltage



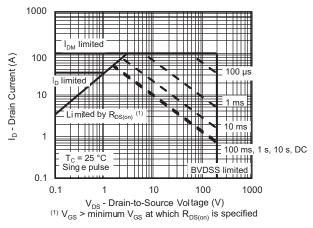
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

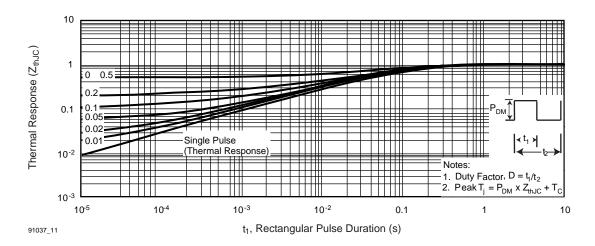


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case





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